

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	475777	semiconductor and (tft or (thin film transistor))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/09/29 15:23
2	BRS	L2	238575	1 and (gate electrode)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/09/29 15:24
3	BRS	L3	52241	2 and (polysilicon or (polycrystal\$4 adj (silicon or si)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/09/29 15:25
4	BRS	L4	25545	"4" and (amorphous adj (silicon or si))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/09/29 15:27
5	BRS	L5	6613	3 and (amorphous adj (silicon or si))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/09/29 15:27

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	Comments	Error Definition	Errors
1			0
2			0
3			0
4			0
5			0

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	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	2015	5 and laser	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/09/29 15:27
7	BRS	L7	85	6 and taper\$3 and angle	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/09/29 15:29
8	BRS	L8	17	7 and (grain adj size)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/09/29 15:29

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	Comments	Error Definition	Errors
6			0
7			0
8			0

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